

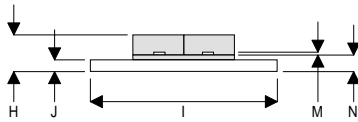
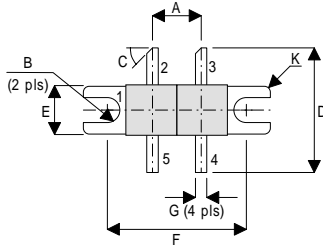


D2208UK

METAL GATE RF SILICON FET

MECHANICAL DATA

**GOLD METALLISED
MULTI-PURPOSE SILICON
DMOS RF FET
40W – 12.5V – 500MHz
PUSH-PULL**



DK

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1
PIN 3 DRAIN 2 PIN 4 GATE 2
PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
A	6.45	0.13	0.254	0.005
B	1.65R	0.13	0.065R	0.005
C	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
H	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.13	0.02	0.005	0.001
N	2.16	0.13	0.085	0.005

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	134W
BV_{DSS}	Drain – Source Breakdown Voltage *	40V
BV_{GSS}	Gate – Source Breakdown Voltage *	$\pm 20V$
$I_{D(sat)}$	Drain Current *	16A
T_{stg}	Storage Temperature	-65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

* Per Side

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PER SIDE					
B _V DSS	Drain–Source Breakdown Voltage	V _{GS} = 0	I _D = 10mA	40	V
I _D DSS	Zero Gate Voltage Drain Current	V _{DS} = 12.5V	V _{GS} = 0	8	mA
I _G DSS	Gate Leakage Current	V _{GS} = 20V	V _{DS} = 0	4	μA
V _{GS(th)}	Gate Threshold Voltage *	I _D = 10mA	V _{DS} = V _{GS}	0.5	V
g _{fs}	Forward Transconductance *	V _{DS} = 10V	I _D = 1.6A	1.44	S
TOTAL DEVICE					
G _{PS}	Common Source Power Gain	P _O = 40W		10	dB
η	Drain Efficiency	V _{DS} = 12.5V	I _{DQ} = 1.6A	40	%
VSWR	Load Mismatch Tolerance	f = 500MHz		20:1	—
PER SIDE					
C _i SS	Input Capacitance	V _{DS} = 0	V _{GS} = -5V f = 1MHz		96 pF
C _o SS	Output Capacitance	V _{DS} = 12.5V	V _{GS} = 0 f = 1MHz		80 pF
C _r SS	Reverse Transfer Capacitance	V _{DS} = 12.5V	V _{GS} = 0 f = 1MHz		8 pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 1.3°C / W
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